



DTV32G-1500B

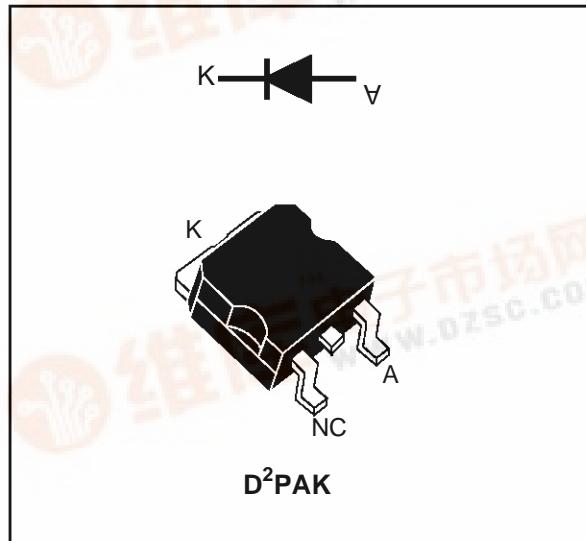
(CRT HORIZONTAL DEFLECTION)
HIGH VOLTAGE DAMPER DIODE

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	6 A
V_{RRM}	1500 V
V_F (max)	1.5 V

FEATURES AND BENEFITS

- HIGH BREAKDOWN VOLTAGE CAPABILITY
- HIGH FREQUENCY OPERATION
- SPECIFIED TURN ON SWITCHING CHARACTERISTICS
- TYPICAL TOTAL LOSSES: 3.5 W ($I_{Fpeak} = 6$ A, $F = 56$ kHz)
- SUITABLE WITH BUH TRANSISTORS SERIES
- SMD PACKAGE



DESCRIPTION

High voltage diode especially designed for horizontal deflection stage in standard and high resolution displays for TV's and monitors.

This device is packaged in D²PAK.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_{F(RMS)}$	RMS forward current	15	A
V_{RRM}	Repetitive Peak Reverse Voltage	1500	V
V_{RWM}	Reverse Working Voltage	1350	V
$I_{F(AV)}$	Average forward current $\delta = 0.5$	6	A
I_{FSM}	Surge Non Repetitive Forward Current $t_p = 10ms$ sinusoidal	100	A
T_{stg}	Storage Temperature	- 40 to 150	°C
T_j	Maximum Operating Junction Temperature	150	

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THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to Case	2	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Min	Typ	Max	Unit
I_R *	$V_R = V_{RWM}$	$T_j = 25^\circ C$		200	μA
		$T_j = 100^\circ C$		1	mA
V_F **	$I_F = 6A$	$T_j = 25^\circ C$		1.5	V
		$T_j = 100^\circ C$		1.4	

pulse test : * $t_p = 5 \text{ ms}$, $\delta < 2\%$

** $t_p = 380 \mu s$, $\delta < 2\%$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min	Typ	Max	Unit
$t_{rr}(1)$	$T_j = 25^\circ C$	$I_F = 1 A \quad dI_F/dt = -50 A/\mu s \quad V_R = 30V$			175	ns
		$I_F = 1 A \quad dI_F/dt = -15 A/\mu s \quad V_R = 30V$			250	
t_{rr}	$T_j = 25^\circ C$	$I_F = 1 A \quad I_R = 100mA$		140		ns

TURN-ON SWITCHING CHARACTERISTICS

Symbol	Test Conditions		Min	Typ	Max	Unit
$t_{fr}(2)$	$T_j = 100^\circ C$	$I_F = 6 A \quad dI_F/dt = 80 A/\mu s$		0.6		μs
$V_{Fp}(2)$		$V_{FR} = 2 V$		39		V

(1) Test following JEDEC standard

(2) Test representative of the application

To evaluate the maximum conduction losses use the following equation :

$$V_F = 1.2 + 0.034 I_F \quad P = 1.2 \times I_F(\text{av}) + 0.034 \times I_F^2 (\text{RMS})$$

Fig. 1: Average forward power dissipation versus average forward current.

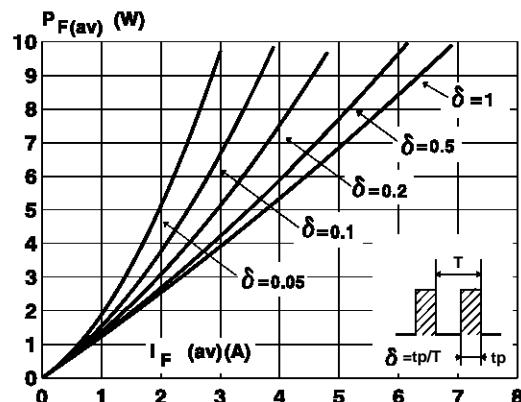


Fig. 3: Average current versus ambient temperature.

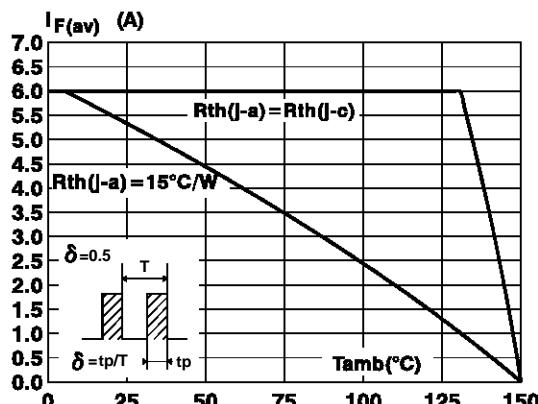


Fig. 5: Relative variation of thermal transient impedance junction to case versus pulse duration.

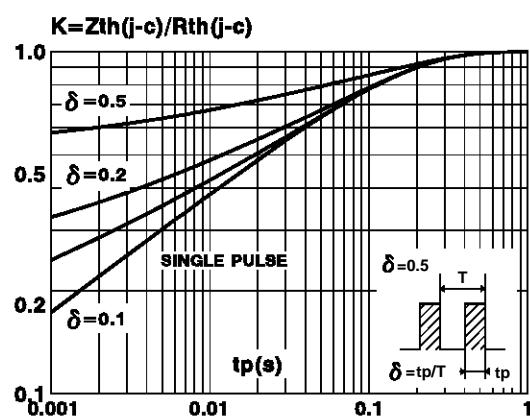


Fig. 2: Peak current versus form factor.

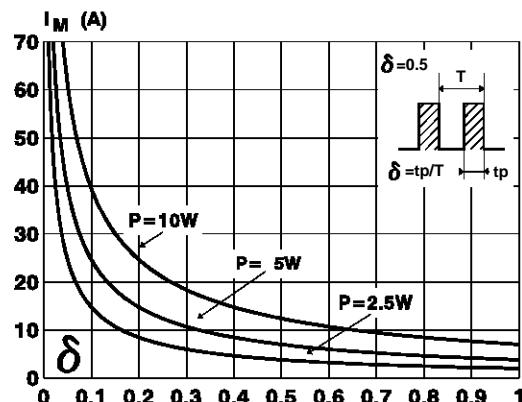


Fig. 4: Non repetitive surge peak forward current versus overload duration (maximum values).

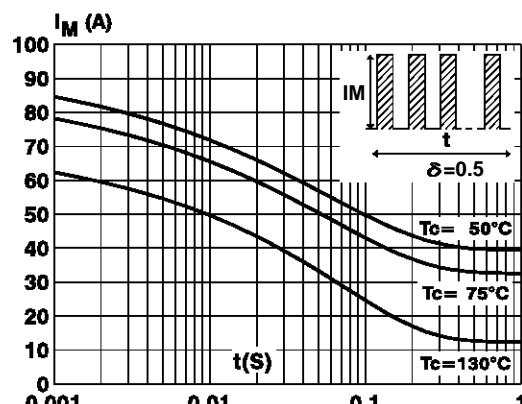
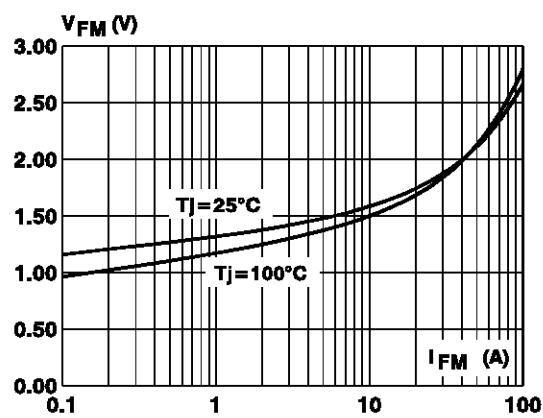


Fig. 6: Forward voltage drop versus forward current (maximum values).



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Fig. 7: Junction capacitance versus reverse voltage applied (typical values).

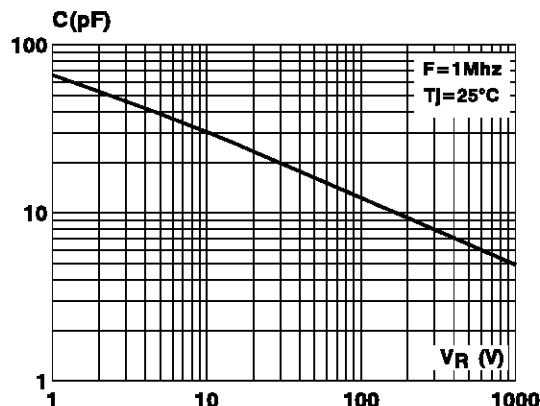


Fig. 9: Peak reverse current versus $\text{d}I_F/\text{d}t$.

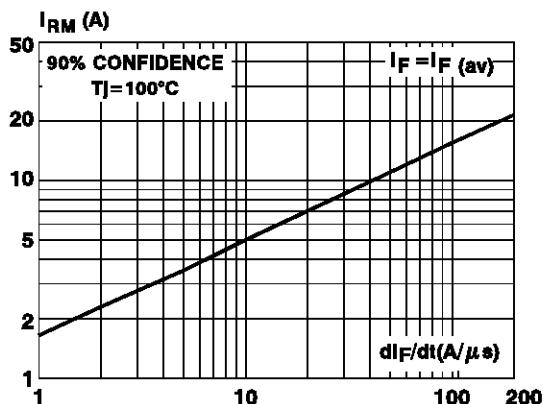


Fig. 11: Recovery time versus $\text{d}I_F/\text{d}t$.

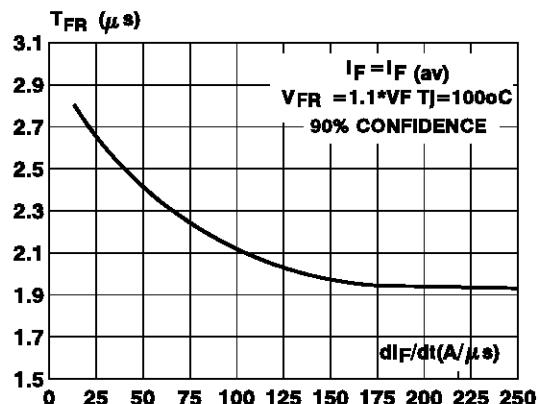


Fig. 8: Recovery charge versus $\text{d}I_F/\text{d}t$.

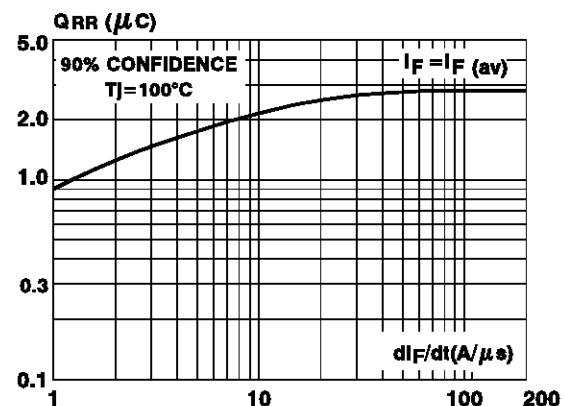


Fig. 10: Dynamic parameters versus junction temperature.

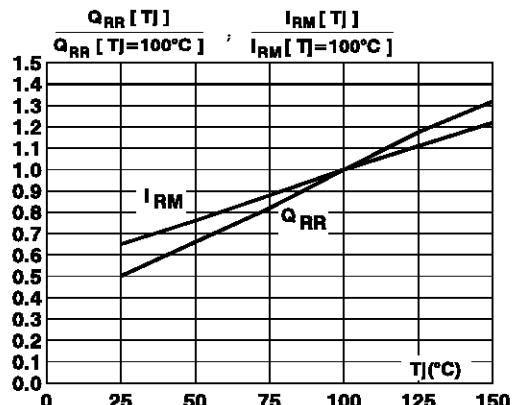
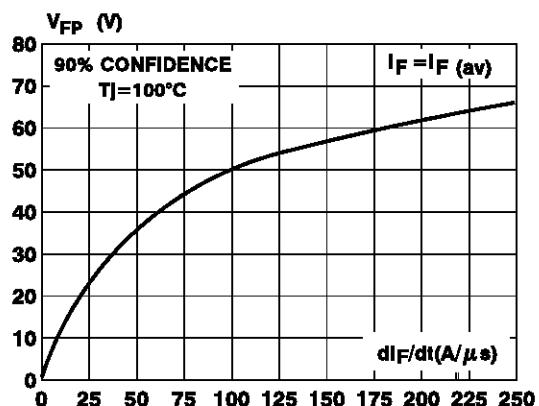
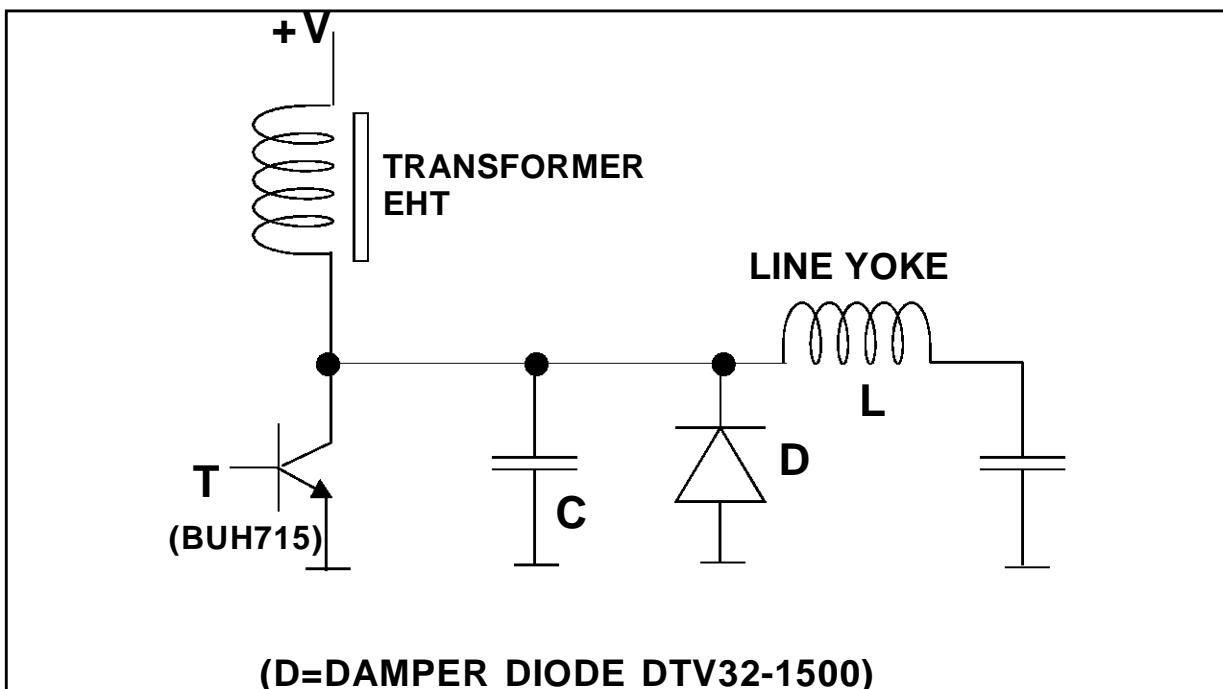


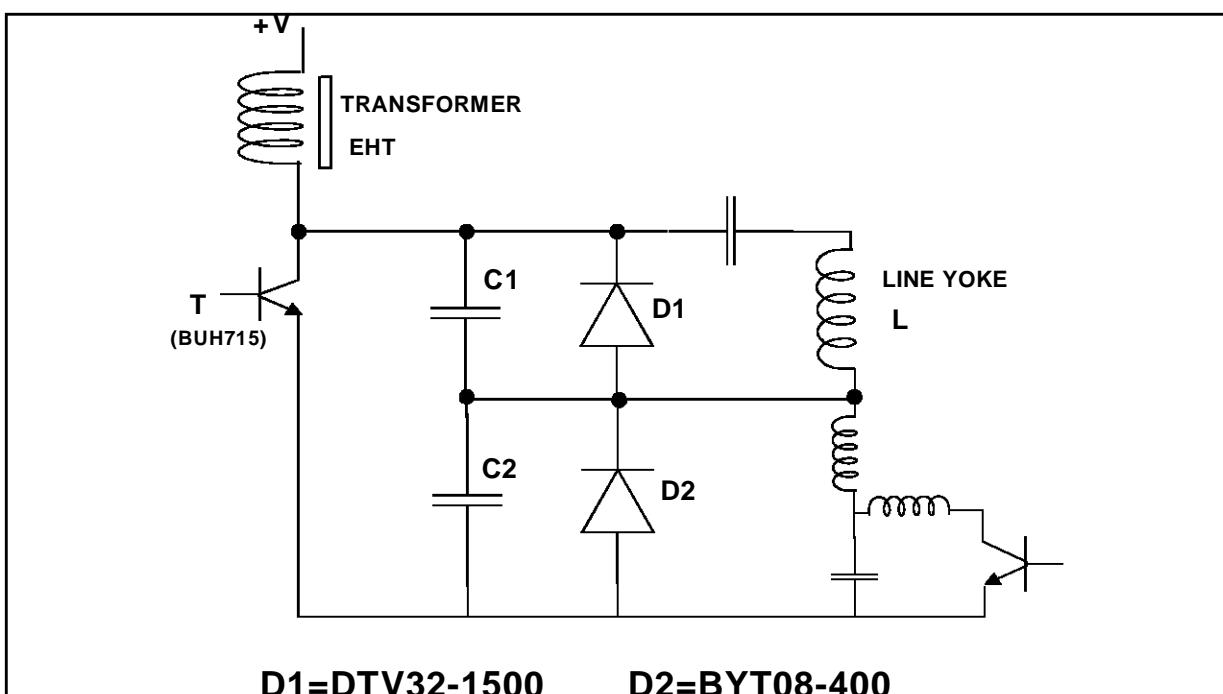
Fig. 12: Peak forward voltage versus $\text{d}I_F/\text{d}t$.



BASIC HORIZONTAL DEFLECTION CIRCUIT



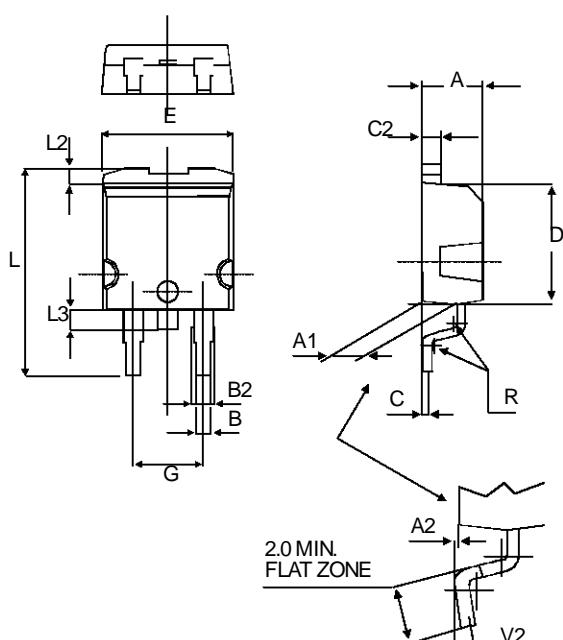
BASIC E-W DIODE MODULATOR CIRCUIT



DTV32G-1500B

PACKAGE DATA

D²PAK



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25		1.40	0.049		0.055
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	9.00		9.35	0.354		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.37	0.050		0.054
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

Marking: DTV32G-1500B

Cooling method : C.

Weight : 1.8 g.

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